Electronic Supplementary Information (ESI)

Electronic structure and optical properties of novel monolayer gallium nitride and boron phosphide heterobilayer

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FIG. S1: Phonon spectra of MGaN/MBP heterobilayers.

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FIG. S2: Energy band spectrum of MGaN and MBP for PBE (solid) and HSE06 (dotted).



FIG. S3: Electronic band diagram of AA, AB1 and AB2 stack of mGaN/MBP heterobilayers in the presence of perpendicular electric field.